

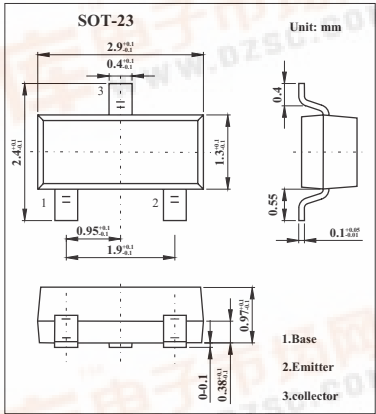
SMD Type

Transistors

Silicon PNP Epitaxial
2SA1468

■ Features

- High voltage amplifier.



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to base voltage	V _{CB0}	-180	V
Collector to emitter voltage	V _{CEO}	-180	V
Emitter to base voltage	V _{EB0}	-5	V
Collector current	I _c	-100	mA
Collector power dissipation	P _c	150	mW
Junction temperature	T _j	150	℃
Storage temperature	T _{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _c = -10 μA, I _E = 0	-180			V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _c = -0.5 mA, R _{BE} = ∞	-180			V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = -10 μA, I _c = 0	-5			V
DC current transfer ratio	h _{FE}	V _{CE} = -12 V, I _c = -2 mA	100		320	
Collector to emitter saturation voltage	V _{CE(sat)}	I _c = -30 mA, I _B = -3 mA			-0.5	V
Base emitter voltage	V _{BE}	V _{CE} = -12 V, I _c = -2 mA			-1	V
Gain bandwidth product	f _T	V _{CE} = -12 V, I _c = -10 mA		200		MHz
Collector output capacitance	C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz		3.5		pF

■ hFE Classification

Marking	INB	INC
Rank	B	C
hFE	100~200	160~320

